

MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM3J66MFV

## 1. Applications

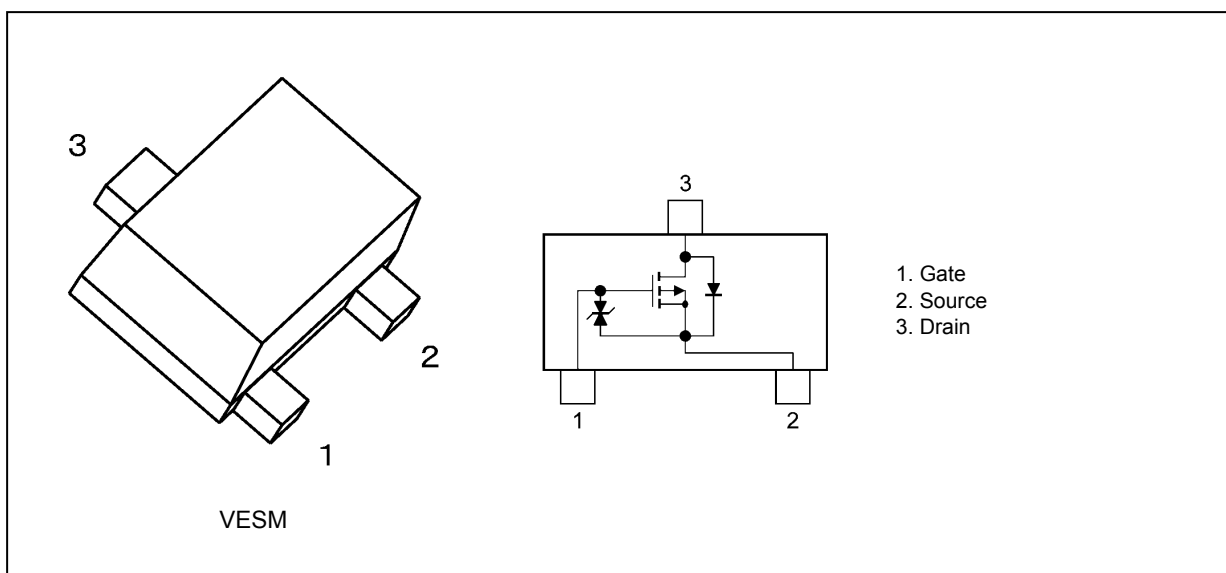
- Load Switches

## 2. Features

- (1) AEC-Q101 qualified (Note 1)
- (2) 1.2-V drive
- (3) Low drain-source on-resistance
  - :  $R_{DS(ON)} = 390 \text{ m}\Omega$  (max) (@ $V_{GS} = -4.5 \text{ V}$ )
  - $R_{DS(ON)} = 480 \text{ m}\Omega$  (max) (@ $V_{GS} = -2.5 \text{ V}$ )
  - $R_{DS(ON)} = 660 \text{ m}\Omega$  (max) (@ $V_{GS} = -1.8 \text{ V}$ )
  - $R_{DS(ON)} = 900 \text{ m}\Omega$  (max) (@ $V_{GS} = -1.5 \text{ V}$ )
  - $R_{DS(ON)} = 4000 \text{ m}\Omega$  (max) (@ $V_{GS} = -1.2 \text{ V}$ )

Note 1: For detail information, please contact to our sales.

## 3. Packaging and Pin Configuration



Start of commercial production

2018-02

## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25\text{ }^{\circ}\text{C}$ )

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DS}$	-20	V
Gate-source voltage	$V_{GS}$	-8/+6	
Drain current (DC) (Note 1)	$I_D$	-0.8	A
Drain current (pulsed) (Note 1), (Note 2)	$I_{DP}$	-1.6	
Power dissipation (Note 3)	$P_D$	150	mW
Power dissipation (Note 4)	$P_D$	500	
Power dissipation (t < 5 s) (Note 4)	$P_D$	800	
Channel temperature	$T_{ch}$	150	$^{\circ}\text{C}$
Storage temperature	$T_{stg}$	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed  $150\text{ }^{\circ}\text{C}$ .

Note 2: Pulse width (PW)  $\leq 1\text{ ms}$ , duty < 1 %

Note 3: Device mounted on an FR4 board.(25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu pad: 0.585 mm<sup>2</sup>)

Note 4: Device mounted on an FR4 board.(25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu pad: 645 mm<sup>2</sup>)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance,  $R_{th(ch-a)}$ , and the drain power dissipation,  $P_D$ , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

## 5. Electrical Characteristics

### 5.1. Static Characteristics (Unless otherwise specified, $T_a = 25\text{ }^{\circ}\text{C}$ )

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = -8/+6\text{ V}$	—	—	$\pm 1$	$\mu\text{A}$
Drain cut-off current	$I_{DSS}$	$V_{DS} = -20\text{ V}$ , $V_{GS} = 0\text{ V}$	—	—	-1	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = -1\text{ mA}$ , $V_{GS} = 0\text{ V}$	-20	—	—	V
Drain-source breakdown voltage (Note 1)	$V_{(BR)DSX}$	$I_D = -1\text{ mA}$ , $V_{GS} = 5\text{ V}$	-15	—	—	
Gate threshold voltage (Note 2)	$V_{th}$	$V_{DS} = -3\text{ V}$ , $I_D = -1\text{ mA}$	-0.3	—	-1.0	
Drain-source on-resistance (Note 3)	$R_{DS(ON)}$	$I_D = -10\text{ mA}$ , $V_{GS} = -1.2\text{ V}$	—	770	4000	$\text{m}\Omega$
		$I_D = -100\text{ mA}$ , $V_{GS} = -1.5\text{ V}$	—	560	900	
		$I_D = -200\text{ mA}$ , $V_{GS} = -1.8\text{ V}$	—	470	660	
		$I_D = -500\text{ mA}$ , $V_{GS} = -2.5\text{ V}$	—	380	480	
		$I_D = -800\text{ mA}$ , $V_{GS} = -4.5\text{ V}$	—	310	390	
Forward transfer admittance (Note 3)	$ Y_{fs} $	$V_{DS} = -3\text{ V}$ , $I_D = -100\text{ mA}$	0.5	1.0	—	S

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (-1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

Take this into consideration when using the device.

Note 3: Pulse measurement.

### 5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25\text{ }^{\circ}\text{C}$ )

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	$C_{iss}$	$V_{DS} = -10\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	—	100	—	$\text{pF}$
Reverse transfer capacitance	$C_{rss}$		—	10	—	
Output capacitance	$C_{oss}$		—	16	—	
Switching time (turn-on time) (Note 1)	$t_{on}$	$V_{DD} = -10\text{ V}$ , $I_D = -200\text{ mA}$ , $V_{GS} = 0\text{ to }-2.5\text{ V}$ , $R_G = 50\text{ }\Omega$	—	8	—	ns
Switching time (turn-off time) (Note 1)	$t_{off}$		—	26	—	

Note 1: Duty  $\leq 1\%$ , input  $t_r$ ,  $t_f < 5\text{ ns}$ , Common source, See Chapter 5.3

### 5.3. Switching Time Test Circuit

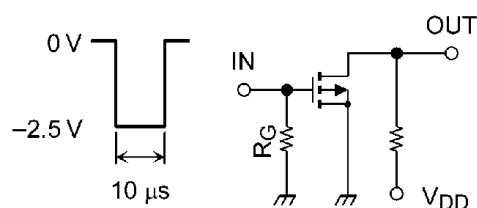


Fig. 5.3.1 Test Circuit of Switching Time

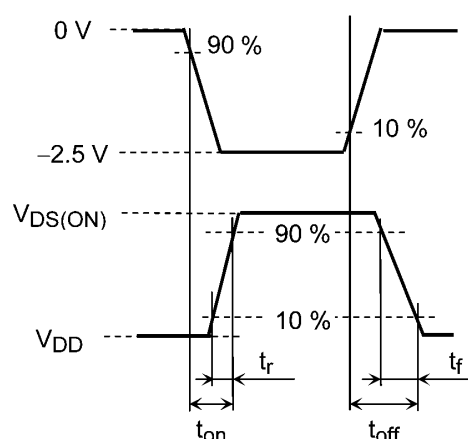


Fig. 5.3.2 Input Waveform/Output Waveform

5.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q <sub>g</sub>	V <sub>DD</sub> = -10 V, I <sub>D</sub> = -800 mA, V <sub>GS</sub> = -4.5 V	—	1.6	—	nC
Gate-source charge 1	Q <sub>gs1</sub>		—	0.2	—	
Gate-drain charge	Q <sub>gd</sub>		—	0.4	—	

5.5. Source-Drain Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Diode forward voltage (Note 1)	V <sub>DSF</sub>	I <sub>D</sub> = 800 mA, V <sub>GS</sub> = 0 V	—	0.9	1.2	V

Note 1: Pulse measurement.

6. Marking

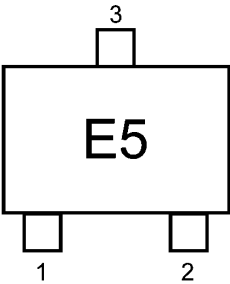
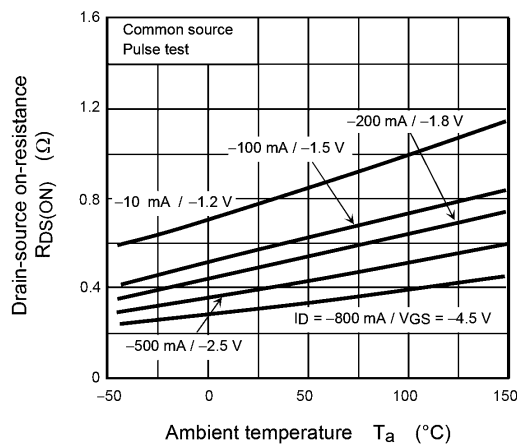
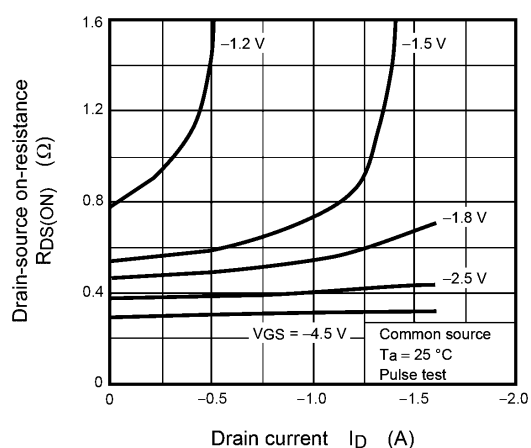
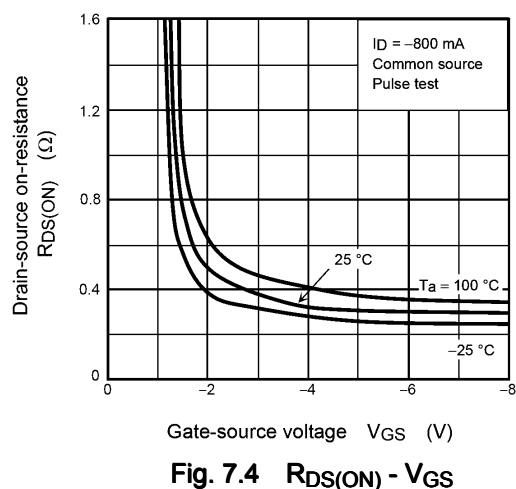
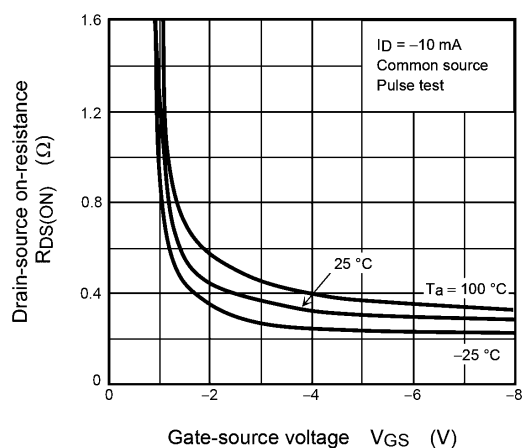
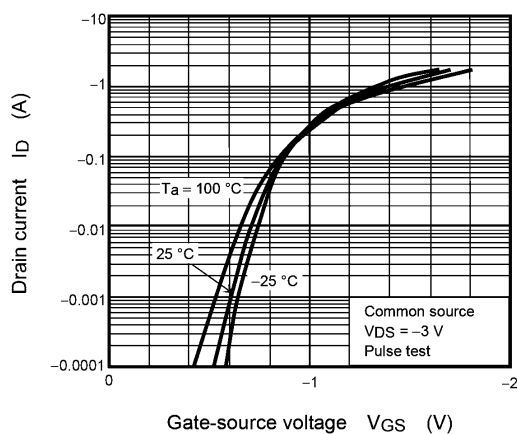
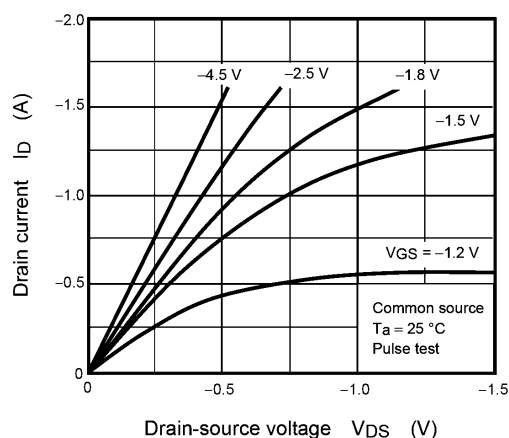


Fig. 6.1 Marking

## 7. Characteristics Curves (Note)



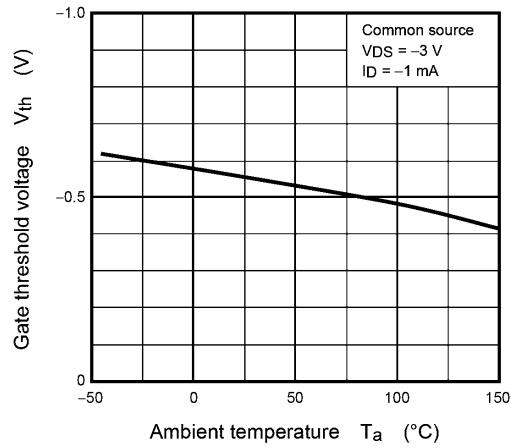


Fig. 7.7  $V_{th} - T_a$

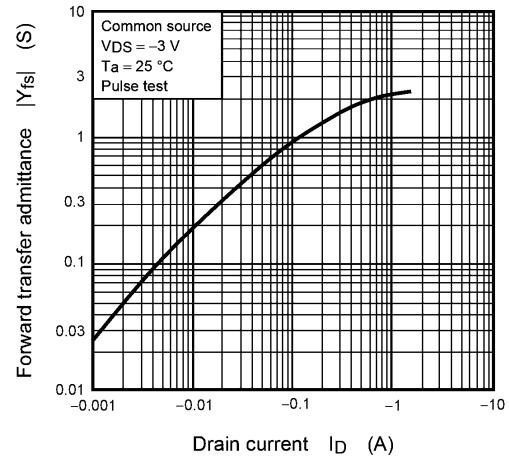


Fig. 7.8  $|Y_{fs}| - I_D$

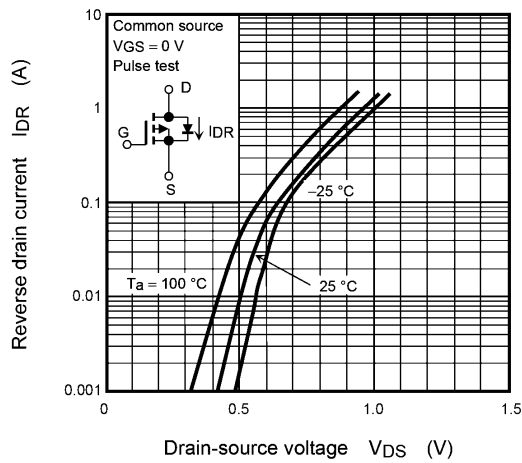


Fig. 7.9  $I_{DR} - V_{DS}$

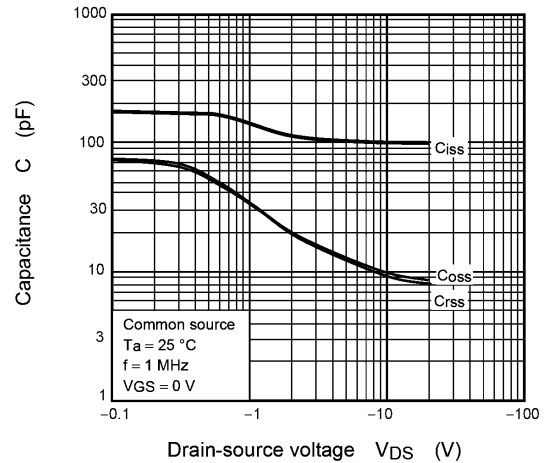


Fig. 7.10  $C - V_{DS}$

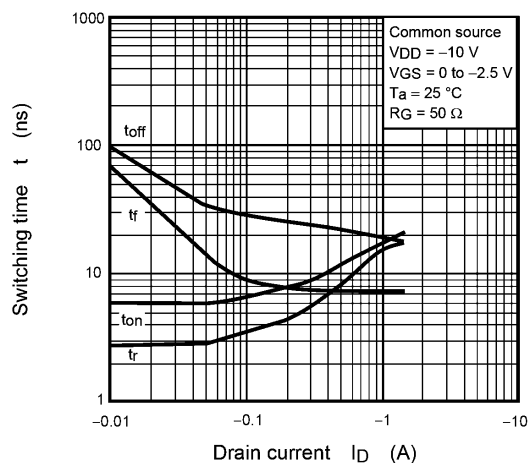


Fig. 7.11  $t - I_D$

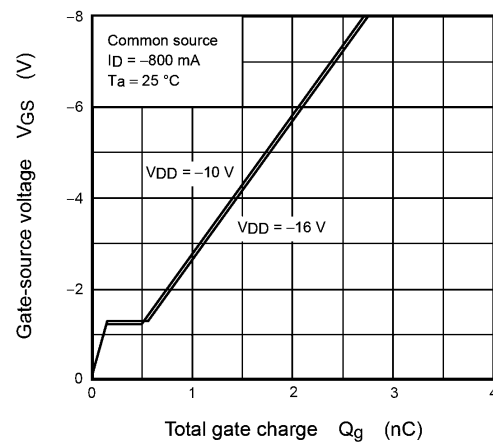


Fig. 7.12 Dynamic Input Characteristics

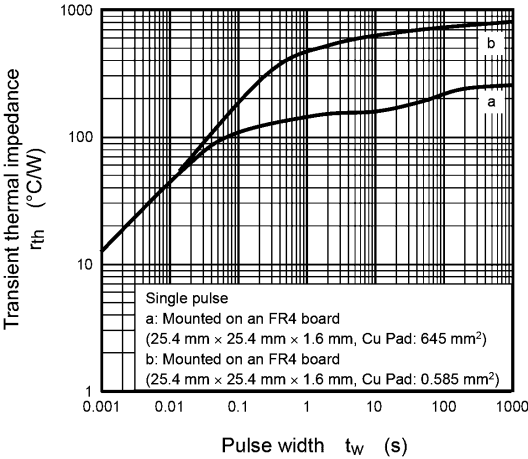


Fig. 7.13  $r_{th} - t_w$

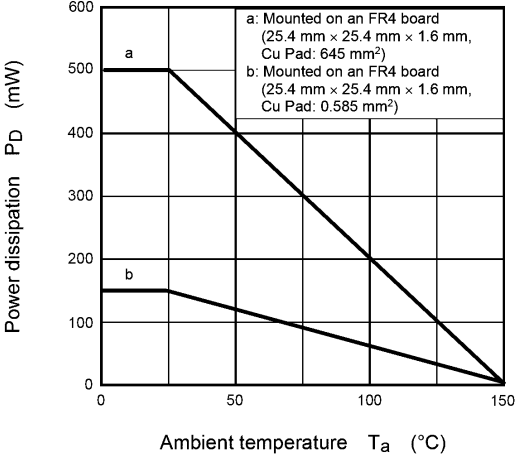
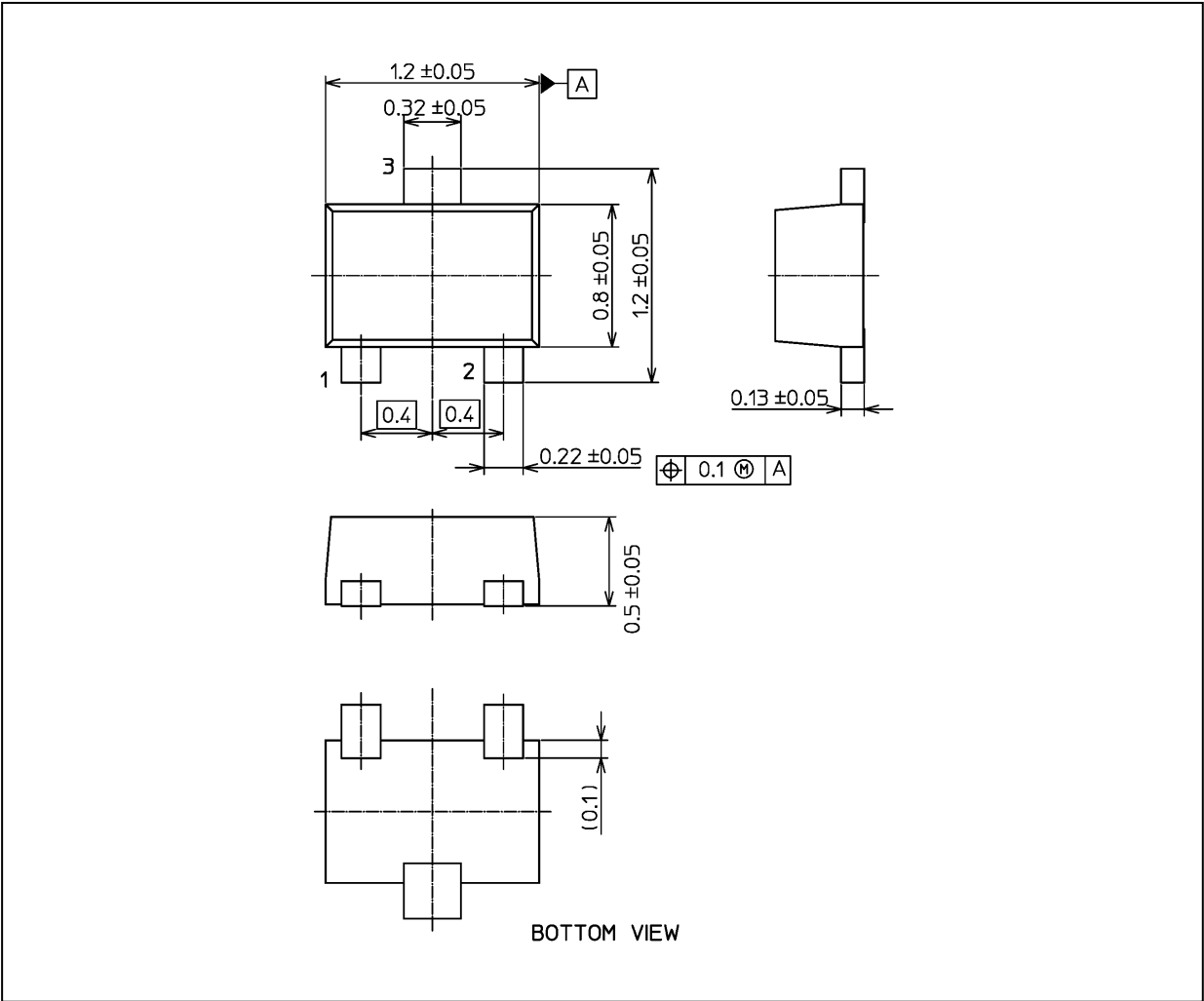


Fig. 7.14  $P_D - T_a$

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 1.5 mg (typ.)

Package Name(s)
TOSHIBA: 1-1Q1S
Nickname: VESM



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